Long V Le

List of Publications by Year
in descending order

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49 papers	722 citations	840776 11 h-index	526287 27 g-index
49 all docs	49 docs citations	49 times ranked	1361 citing authors

#	Article	IF	Citations
1	Azimuthal angle dependent dielectric function of SnS by ellipsometry. Journal of the Korean Physical Society, 2022, 80, 59-62.	0.7	0
2	Modeling the temperature dependence of the optical properties of anisotropic SnS0.52Se0.48. Journal of the Korean Physical Society, 2021, 78, 269-274.	0.7	0
3	A Systematic Study of Compositionally Dependent Dielectric Tensors of SnSxSe1-x Alloys by Spectroscopic Ellipsometry. Crystals, 2021, 11, 548.	2.2	3
4	Maximum-entropy revisited: Optimal filtering of spectra. Journal of Applied Physics, 2021, 129, .	2.5	8
5	Approximated dielectric tensor of the biaxial Î±-SnSe crystal. Journal of the Korean Physical Society, 2021, 78, 297-301.	0.7	1
6	Normal-incidence type solution immersed silicon (SIS) biosensor for ultra-sensitive, label-free detection of cardiac troponin I. Biosensors and Bioelectronics, 2020, 168, 112525.	10.1	5
7	Modeling of the Temperature Dependence of the Dielectric Function of Biaxial Î±-SnS. Journal of the Korean Physical Society, 2020, 77, 987-990.	0.7	0
8	Optical Properties of Anisotropic SnSxSe1â^'x for Arbitrary Compositions. Journal of the Korean Physical Society, 2020, 77, 1178-1182.	0.7	2
9	Anisotropic behavior of excitons in single-crystal Î±-SnS. AIP Advances, 2020, 10, .	1.3	9
10	Temperature dependence of the dielectric function and critical points of Î±-SnS from 27 to 350ÂK. Scientific Reports, 2020, 10, 18396.	3.3	11
11	Modeling of the Optical Properties of Monolayer WS2. Journal of the Korean Physical Society, 2020, 77, 298-302.	0.7	2
12	Partially Spatial Coherent Thermal Emitter Based on an Epsilon-and-mu-near-zero Metamaterial. Journal of the Korean Physical Society, 2020, 76, 889-894.	0.7	0
13	Temperature dependence of optical properties of monolayer WS2 by spectroscopic ellipsometry. Applied Surface Science, 2020, 511, 145503.	6.1	21
14	Quantitative assessment of linear noise-reduction filters for spectroscopy. Optics Express, 2020, 28, 38917.	3.4	7
15	Parameterization of the Dielectric Function of GaAsSb Alloy Films. Journal of the Korean Physical Society, 2020, 77, 840-844.	0.7	1
16	Parameterization of Dielectric Functions and Phase Transitions of SrTiO3 from 26 to 674 K. Journal of Nanoscience and Nanotechnology, 2020, 20, 6692-6697.	0.9	0
17	Multi-photoactive quantum-dot channels for zinc oxide phototransistors by a surface-engineering patterning process. Current Applied Physics, 2019, 19, 992-997.	2.4	9
18	A Parametric Model for Temperature Dependence of Dielectric Function of AlSb Film. Journal of Nanoscience and Nanotechnology, 2019, 19, 6801-6807.	0.9	0

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19	Treatment of Surface Plasmon Resonance (SPR) Background in Total Internal Reflection Ellipsometry: Characterization of RNA Polymerase II Film Formation. Applied Spectroscopy, 2019, 73, 261-270.	2.2	3
20	Dielectric Functions and Critical Points of GaAsSb Alloys. Journal of the Korean Physical Society, 2019, 74, 595-599.	0.7	3
21	Parameterized optical properties of monolayer MoSe2. AIP Advances, 2019, 9, .	1.3	3
22	Sub-microsecond response time deep-ultraviolet photodetectors using Î±-Ga2O3 thin films grown via low-temperature atomic layer deposition. Journal of Alloys and Compounds, 2019, 780, 400-407.	5.5	52
23	Temperature Dependence of the Dielectric Function of Monolayer MoSe2. Scientific Reports, 2018, 8, 3173.	3.3	13
24	Multifunctional Bilayer Template for Near-Infrared-Sensitive Organic Solar Cells. ACS Applied Materials & Interfaces, 2018, 10, 16681-16689.	8.0	3
25	Pt/Alumina Hyperbolic Metafilms with Highâ€Temperature Stability, Wide Wavelength Tunability, and Omnidirectional Absorption. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1800287.	1.8	9
26	Temperature Dependence of the Dielectric Response and Critical Point Energies of Bi1.85Gd0.15Te3. Journal of Nanoscience and Nanotechnology, 2018, 18, 6321-6325.	0.9	0
27	Ordered Nanoscale Heterojunction Architecture for Enhanced Solutionâ€Based CuInGaS₂ Thin Film Solar Cell Performance. Advanced Energy Materials, 2016, 6, 1601114.	19.5	11
28	Optical characterization of the PtSi/Si by using spectroscopic ellipsometry. Journal of the Korean Physical Society, 2016, 69, 291-296.	0.7	0
29	Temperature dependence of the critical points of monolayer MoS₂by ellipsometry. Applied Spectroscopy Reviews, 2016, 51, 621-635.	6.7	27
30	Analytic representation of the dielectric function of GaN for temperatures from 26 to 690 K. Journal of the Korean Physical Society, 2014, 65, 733-738.	0.7	2
31	Ellipsometric study of the temperature dependences of the dielectric function and the critical points of AlSb at temperatures from 300 to 803 K. Journal of the Korean Physical Society, 2014, 65, 515-519.	0.7	1
32	Analytic determination of the dielectric function of InSb at energies from 0.74 to 6.42 eV at temperatures from 31 to 675 K. Journal of the Korean Physical Society, 2014, 64, 1872-1877.	0.7	1
33	Effect of post-annealing temperature on the dielectric function of solution-processed LaAlO x /Si Films. Journal of the Korean Physical Society, 2014, 64, 1509-1513.	0.7	0
34	Parametric modeling of the dielectric function and identification of the critical point of a CdMgTe alloy in the vacuum ultraviolet spectral range. Journal of the Korean Physical Society, 2012, 60, 1219-1223.	0.7	0
35	Pressure-induced resonance Raman effect of InAs x P1â^'x alloy films on InP. Journal of the Korean Physical Society, 2012, 61, 1573-1577.	0.7	0
36	Parametric model dielectric functions of InAs for temperatures from 22 to 675 K. Journal of the Korean Physical Society, 2012, 61, 1821-1825.	0.7	4

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37	Investigation of InSb critical-point energies at 25 K by using spectroscopic ellipsometry. Journal of the Korean Physical Society, 2012, 61, 439-443.	0.7	1
38	Dielectric function and energy of the E 0 critical point of hexagonal GaN at 26 K studied by using spectroscopic ellipsometry. Journal of the Korean Physical Society, 2012, 61, 791-794.	0.7	2
39	Temperature dependence of the dielectric function and critical-point energies of InAs. Journal of the Korean Physical Society, 2012, 61, 97-101.	0.7	6
40	Effect of annealing temperature on microstructural evolution and electrical properties of sol-gel processed ZrO2/Si films. Applied Physics Letters, 2011, 98, .	3.3	54
41	InAs critical-point energies at 22 K from spectroscopic ellipsometry. Applied Physics Letters, 2010, 97, 171912.	3.3	21
42	Interference effect on Raman spectrum of graphene on<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>SiO</mml:mtext></mml:mrow><mml:mn>2</mml:mn></mml:msu Physical Review B, 2009, 80, .	3.2	255
43	Optical nanometrology of Au nanoparticles on a multilayer film. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1194-1197.	0.8	3
44	Characterization of Si nanorods by spectroscopic ellipsometry with efficient theoretical modeling. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 876-879.	1.8	31
45	Precision auto-alignment for the specimen stage of an ellipsometer. Review of Scientific Instruments, 2002, 73, 2988-2993.	1.3	1
46	Effects of growth interruption on the evolution of InAs/InP self-assembled quantum dots. Journal of Electronic Materials, 2000, 29, 535-541.	2.2	15
47	Analysis of P adsorption and desorption on the (001) InP surface using surface photoabsorption. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1999, 17, 2663-2667.	2.1	9
48	Effects of As/P exchange reaction on the formation of InAs/InP quantum dots. Applied Physics Letters, 1999, 74, 2029-2031.	3.3	113
49	In-situ observation of As/P exchange reaction and As carryover in InAs/InP quantum well structures by surface photoabsorption. , 0, , .		0